

**To the Claims:**

Claim 1. (currently amended) A semiconductor cleaning method, ~~comprising~~  
consisting of:

~~providing a semiconductor wafer;~~  
~~forming a first layer of oxide over the semiconductor wafer;~~  
~~forming a floating gate layer over the first layer of oxide;~~  
~~forming a second layer of oxide over the floating gate layer;~~  
~~etching the first layer of oxide, the floating gate layer, and the second layer of~~  
~~oxide to form a gate structure;~~  
~~performing a cleaning process to the semiconductor wafer, wherein the cleaning~~  
~~process is consisting of following steps:~~  
  
rinsing ~~[[the]]~~a semiconductor wafer including ~~[[the]]~~a gate structure using an  
ozonated de-ionized (DI) water;  
  
further rinsing the ozonated water-rinsed semiconductor wafer using a ~~[[first]]~~  
cleaning solution, wherein the ~~[[first]]~~ cleaning solution is a ~~HF:HCl:H<sub>2</sub>O solution or at~~  
~~least one of H<sub>2</sub>O:H<sub>2</sub>O<sub>2</sub>:NH<sub>4</sub>OH solution and H<sub>2</sub>O:H<sub>2</sub>O<sub>2</sub>:HCl solution;~~ and  
  
additionally rinsing the further rinsed semiconductor wafer using the ozonated DI  
water.

Claim 2. (canceled).

Claim 3. (original) The method of claim 1, wherein the semiconductor wafer has formed therein at least one device.

Claim 4. (original) The method of claim 1, wherein the semiconductor wafer has accumulated thereon contaminants accumulated during at least one previous processing step.

Claim 5. (previously presented) The method of claim 4, wherein the contaminants comprise polymer.

Claim 6. (original) The method of claim 5, wherein the polymer comprises photoresist.

Claims 7-11(canceled)

Claim 12. (original) The method of claim 1, wherein the concentration of ozone in the ozonated DI water is within the range of 10-80 ppm.

Claim 13. (original) The method of claim 12, wherein the concentration of ozone in the ozonated DI water is 40 ppm.

Claims 14-20. (canceled)